BGU7032 1 GHz wideband low-noise amplifier with bypass Rev. 2 – 14 September 2010 Pro-

Product data sheet

1. Product profile

1.1 General description

The BGU7032 MMIC is a wideband amplifier with bypass mode. It is designed specifically for high linearity, low-noise applications over a frequency range of 40 MHz to 1 GHz. It is especially suited to Set-Top Box applications.

The LNA is housed in a 6-pin SOT363 plastic SMD package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Internally biased
- Programmable between G_p = 10 dB and bypass
- Flat gain between 40 MHz and 1 GHz
- Noise figure of 4.5 dB
- High linearity with an IP3_O of 29 dBm
- **75** Ω input and output impedance
- Power-down during bypass mode
- Bypass mode current consumption < 5 mA</p>
- ESD protection > 2 kV Human Body Model (HBM) on all pins

1.3 Applications

- Terrestrial and cable Set-Top Boxes (STB)
- Silicon and "Can" tuners
- Personal and Digital Video Recorders (PVR and DVR)
- Home networking and in-house signal distribution



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1.4 Quick reference data

Table 1. Quick reference data

 T_{amb} = 25 °C; typical values at V_{CC} = 5 V; Z_S = Z_L = 75 Ω ; R_{bias} = 43 Ω ; 40 MHz $\leq f_1 \leq$ 1000 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CC}	supply voltage	RF input AC coupled		4.75	5.0	5.25	V
I _{CC(tot)}	total supply current	G _p = 10 dB mode	<u>[1]</u>	-	43	-	mA
		bypass mode	[1]	-	4	-	mA
T _{amb}	ambient temperature			-10	-	+70	°C
NF	noise figure	G _p = 10 dB mode	[1]	-	4.5	-	dB
		bypass mode	[1]	-	2.5	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	1 GHz; G _p = 10 dB mode	<u>[1]</u>	-	14	-	dBm
IP3 ₀	output third-order intercept point	$G_p = 10 \text{ dB mode}$	[1][2]	-	29	-	dBm

[1] Mode depends on setting of V_{CTRL} ; see <u>Table 8</u>.

[2] The fundamental frequency (f₁) is 1000 MHz. The intermodulation product (IM3) is $2 \times f_2 - f_1$, where $f_2 = f_1 \pm 1$ MHz. Input power $P_i = -10$ dBm.

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	RF_OUT		
2	V _{CC}		\mathbf{N}^{3}
3	n.c.		6 - 1
4	CTRL		
5	GND	□1 □2 □3	5 4 sym141
6	RF_IN		,

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BGU7032	-	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4. Marking o	odes
Type number	Marking code
BGU7032	SD%

Note: % character indicates the location of production.

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5. Limiting values

Table 5. In accorda	Table 5. Limiting values In accordance with the Absolute Maximum Rating System (IEC 60134).					
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage	RF input AC coupled		-0.6	5.25	V
V _{ctrl(Gp)}	power gain control voltage	pin CTRL	[1]	0	V _{CC}	V
I _{CC(tot)}	total supply current			-	60	mA
P _{tot}	total power dissipation	$T_{sp} \le 100 \ ^{\circ}C$	[2]	-	250	mW
Pi	input power	single tone		-	10	dBm
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-10	+70	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); according to JEDEC standard 22-A114E		2	-	kV

[1] V_{ctrl(Gp)} must not exceed V_{CC}; I_{CTRL} must be limited to 5 mA (maximum).

[2] T_{sp} is the temperature at the solder point of the ground lead.

Remark: V_{ctrl(Gp)} must not exceed V_{CC}; I_{CTRL} must be limited to a maximum of 5 mA.

6. Thermal characteristics

Table 6.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		240	K/W

7. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C; typical values at V_{CC} = 5 V; Z_S = Z_L = 75 Ω ; R_{bias} = 43 Ω ; 40 MHz \leq $f_1 \leq$ 1000 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CC}	supply voltage	RF input AC coupled		4.75	5.0	5.25	V
I _{CC(tot)}	total supply current	G _p = 10 dB mode	[1]	-	43	-	mA
		bypass mode	[1]	-	4	-	mA
$ s_{21} ^2$	insertion power gain	$G_p = 10 \text{ dB mode}$	[1]	-	10	-	dB
		bypass mode	[1]	-	-2	-	dB
SL _{sl}	slope straight line			-	-1	-	dB
FL	flatness of frequency response			-	-0.2	-	dB
NF	noise figure	$G_p = 10 \text{ dB mode}$	[1]	-	4.5	-	dB
		bypass mode	[1]	-	2.5	-	dB
RL _{in}	input return loss	$G_p = 10 \text{ dB mode}$	[1]	-	18	-	dB
		bypass mode	[1]	-	8	-	dB

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	Table 7.	Characteristics	continued
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 T_{amb} = 25 °C; typical values at V_{CC} = 5 V; Z_S = Z_L = 75 Ω ; R_{bias} = 43 Ω ; 40 MHz \leq $f_1 \leq$ 1000 MHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
RL _{out}	output return loss	$G_p = 10 \text{ dB mode}$	[1]	-	12	-	dB
		bypass mode	[1]	-	8	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	1 GHz; $G_p = 10 \text{ dB}$ mode	[1]	-	14	-	dBm
IP3 ₀	output third-order intercept point	G _p = 10 dB mode	[1][2]	-	29	-	dBm
		bypass mode	[1][2]	-	29	-	dBm

[1] Mode depends on setting of $V_{ctrl(Gp)}$ (V_{CTRL}); see <u>Table 8</u>.

[2] The fundamental frequency (f₁) is 1000 MHz. The intermodulation product (IM3) is $2 \times f_2 - f_1$, where $f_2 = f_1 \pm 1$ MHz. Input power $P_i = -10$ dBm.

Table 8.Gain selection (pin CTRL)

 $-10 \text{ °C} \leq T_{amb} \leq +70 \text{ °C}$; recommended power-up condition: $V_{CTRL} = \text{logic } 0 \text{ or } < 0.7 \text{ V}$.

V _{ctrl(Gp)} (V _{CTRL}) (V)	Mode
≤ 0.7	bypass
≥ 4.3	$G_p = 10 \text{ dB}$

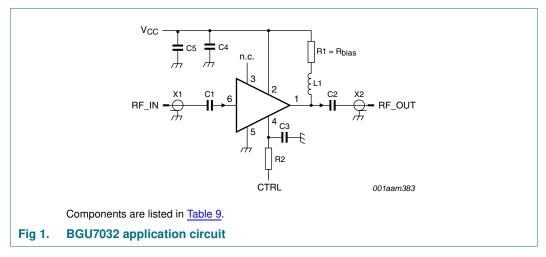
Remark: V_{ctrl(Gp)} must not exceed V_{CC}; I_{CTRL} must be limited to a maximum of 5 mA.

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8. Application information

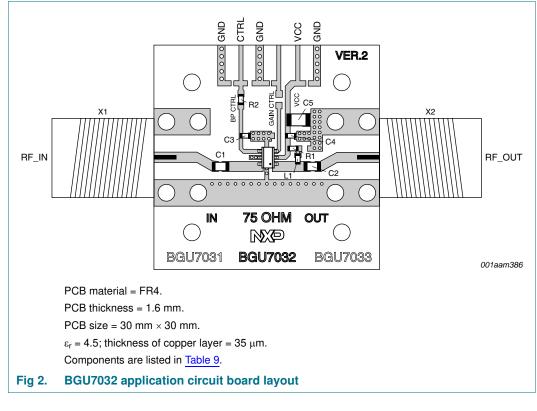
Other applications are possible. Please contact your local sales representative for more information. Application notes are available on the NXP website.

8.1 Application circuit



All control and supply lines must be decoupled properly. The decoupling capacitors must be placed as close to the device as possible.

8.2 Application circuit board layout



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Table 9.List of componentsSee Figure 1 and Figure 2

See <u>Figure 1</u> ar	nd <u>Figure 2</u> .				
Component	Description	Value		Remarks	Function
C1, C2	capacitor	10 nF			DC blocking
C3, C4	capacitor	10 nF			decoupling
C5	capacitor	10 μF			decoupling
L1	chip ferrite bead	$1.5 \ \text{k}\Omega$	[1]	Murata BLM18HE152SN1DF	RF choke
R1	resistor	43 Ω	[1]	R _{bias}	bias setting
R2	resistor	1.8 kΩ			current limiting
X1, X2	connector	75 Ω		F-connector, edge mount PCB reflow type, Bomar 861V509ERG	input/output

[1] L1 and R1 must have a power rating of 0.1 W or higher.

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9. Package outline

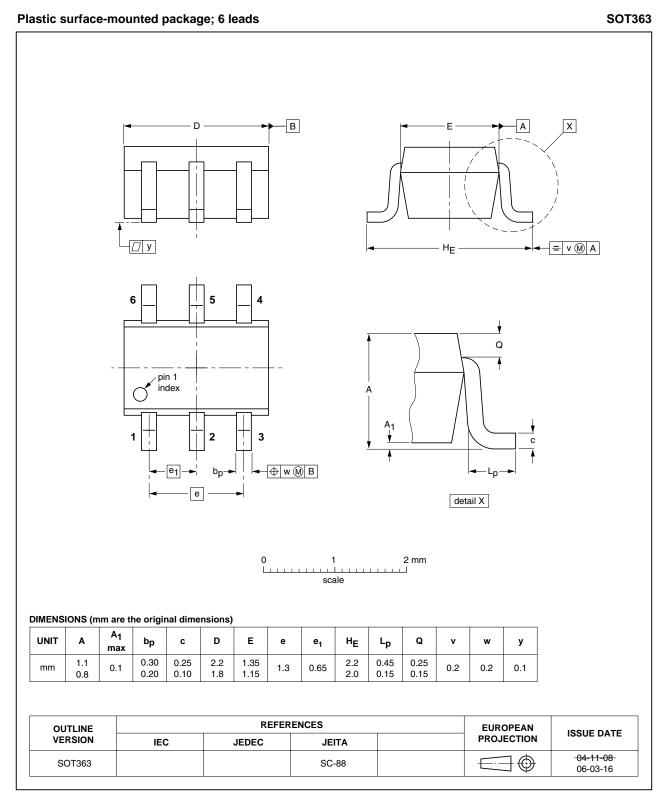


Fig 3. Package outline SOT363

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10. Abbreviations

Table 10. Abbreviations		
Acronym	Description	
AC	Alternating Current	
DC	Direct Current	
LNA	Low-Noise Amplifier	
MMIC	Monolithic Microwave Integrated Circuit	
PCB	Printed-Circuit Board	
RF	Radio Frequency	
SMD	Surface-Mounted Device	

11. Revision history

Document IDRelease dateData sheet statusChange noticeBGU7032 v.220100914Product data sheet-Modifications:• The status of this data sheet has been changed to Product dataBGU7032 v.120100817Preliminary data sheet				history	Table 11. Revision
Modifications: • The status of this data sheet has been changed to Product data	Supersedes	Change notice	Data sheet status	Release date	Document ID
	BGU7032 v.1	-	Product data sheet	20100914	BGU7032 v.2
BGU7032 v.1 20100817 Preliminary data sheet -	a sheet.	changed to Product data	of this data sheet has been c	The status	Modifications:
	-	-	Preliminary data sheet	20100817	BGU7032 v.1

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12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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